

Top View

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Vishay Siliconix

### N-Channel 20 V (D-S) Fast Switching MOSFET

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**Bottom View** 

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	20
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0053
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0078
Q <sub>g</sub> typ. (nC)	14
I <sub>D</sub> (A)	21.1
Configuration	Single

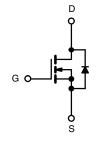
#### **FEATURES**

- TrenchFET® Gen II power MOSFET
- PWM optimized
- 100 % R<sub>q</sub> tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

- Synchronous rectification
- Synchronous buck



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH110DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (	T <sub>A</sub> = 25 °C, unless	otherwise no	ted)			
PARAMETER		SYMBOL	10 s	STEADY STATE	UNIT	
Drain-source voltage		V <sub>DS</sub>	20	20	V	
Gate-source voltage		V <sub>GS</sub>	± 20	± 20	V	
Continuous drain current (T <sub>.I</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	21.1	13.5		
Continuous drain current (1) = 150 °C) "	T <sub>A</sub> = 70 °C		16.9	10.8		
Pulsed drain current		I <sub>DM</sub>	60	60	Α	
Continuous source current (diode conduction) a		I <sub>S</sub>	3.2	1.3		
Single avalanche current	L = 0.1 mH	I <sub>AS</sub>	35	35		
Single avalanche energy	L=UIMH	E <sub>AS</sub>	61	61	mJ	
Maximum navver discination 3	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.8	1.5	W	
Maximum power dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		2	0.8	VV	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150			
Soldering recommendations (peak temperature) b, c		-	260		°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a</sup>	t ≤ 10 s	В	24	33	
Waximum junction-to-ambient -	Steady state	R <sub>thJA</sub>	65	81	°C/W
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	1.9	2.4	

#### Notes

- a. Surface mounted on 1" x 1" FR4 board
- a. Surface modified (www.vishay.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C	C, unless oth	nerwise noted)				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1.5	-	2.5	V
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	la sa	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C	-	-	5	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 V$ , $V_{GS} = 10 V$	40	-	-	Α
Drain-source on-state resistance a	В	$V_{GS} = 10 \text{ V}, I_D = 21.1 \text{ A}$	-	0.0044	0.0053	0
Diaiii-source oii-state resistance "	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 17.4 \text{ A}$	-	0.0064	0.0078	V nA μA A
Forward transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 21.1 A	-	71	-	S
Diode forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 3.2 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
Dynamic <sup>b</sup>						
Total gate charge	$Q_g$		-	14	21	nC
Gate-source charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 21.1 \text{ A}$	-	7	-	
Gate-drain charge	$Q_{gd}$		-	4.5	-	
Gate resistance	$R_g$	f = 1 MHz	0.7	1.4	2.1	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	12	20	
Rise time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$	-	10	15	
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong 1$ A, $V_{GEN} = 10$ V, $R_g = 6$ $\Omega$	=	36	55	ns
Fall time	t <sub>f</sub>		-	10	15	
Body diode reverse recovery time	t <sub>rr</sub>		-	30	60	
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 3.2 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s}$	-	25	50	nC
Reverse recovery fall time	ta	$_{1F} = 3.2 \text{ A}, \text{ u/u} = 100 \text{ A/} \mu \text{s}$	-	14	-	no
Reverse recovery rise time	t <sub>b</sub>		-	16	-	ns

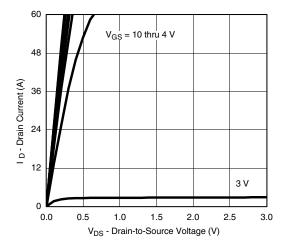
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

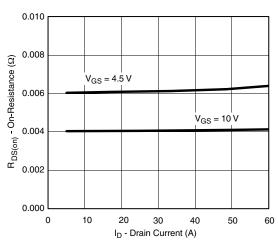
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



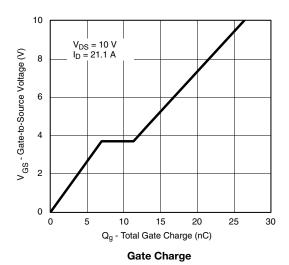
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

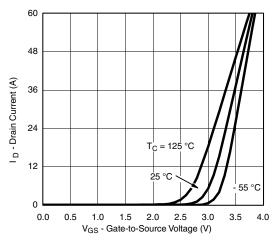


#### **Output Characteristics**

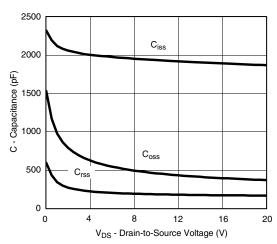


On-Resistance vs. Drain Current

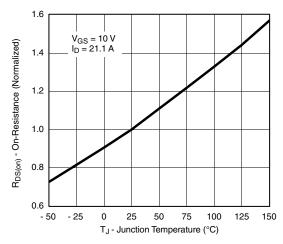




**Transfer Characteristics** 



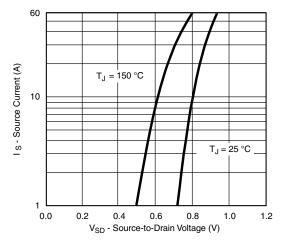
Capacitance



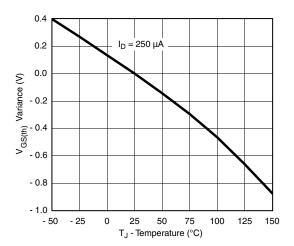
On-Resistance vs. Junction Temperature



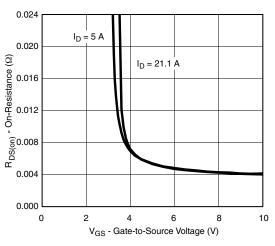
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



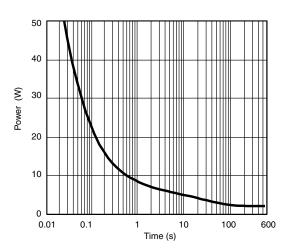
#### Source-Drain Diode Forward Voltage



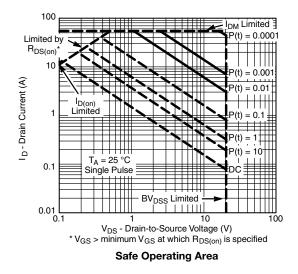
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage

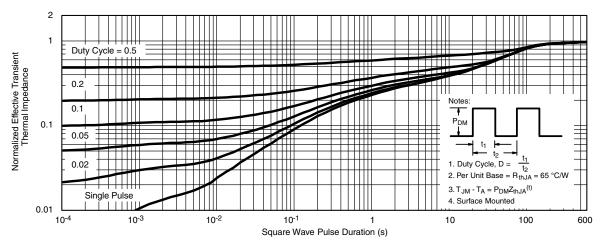


Single Pulse Power, Junction-to-Ambient

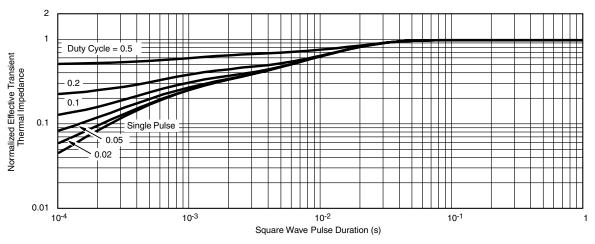




#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



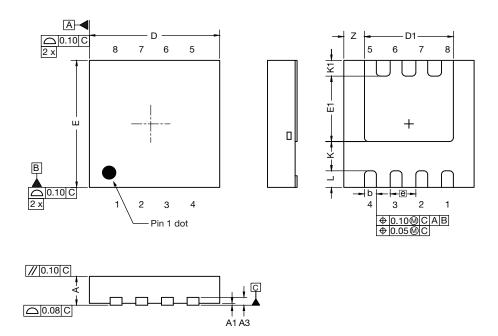
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?79230">http://www.vishay.com/ppg?79230</a>.



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## Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH



DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.			0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е	0.65 bsc.			0.026 bsc.			
K	0.76 ref.			0.030 ref.			
K1	0.41 ref.		0.016 ref.				
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			0.021 ref.			

DWG: 6062



#### RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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